

Device Modeling Report

COMPONENTS:
DIODE/GENERAL PURPOSE RECTIFIER/ STANDARD
PART NUMBER: SF20LC30
MANUFACTURER: SHINDENGEN
REMARK: TC=25C

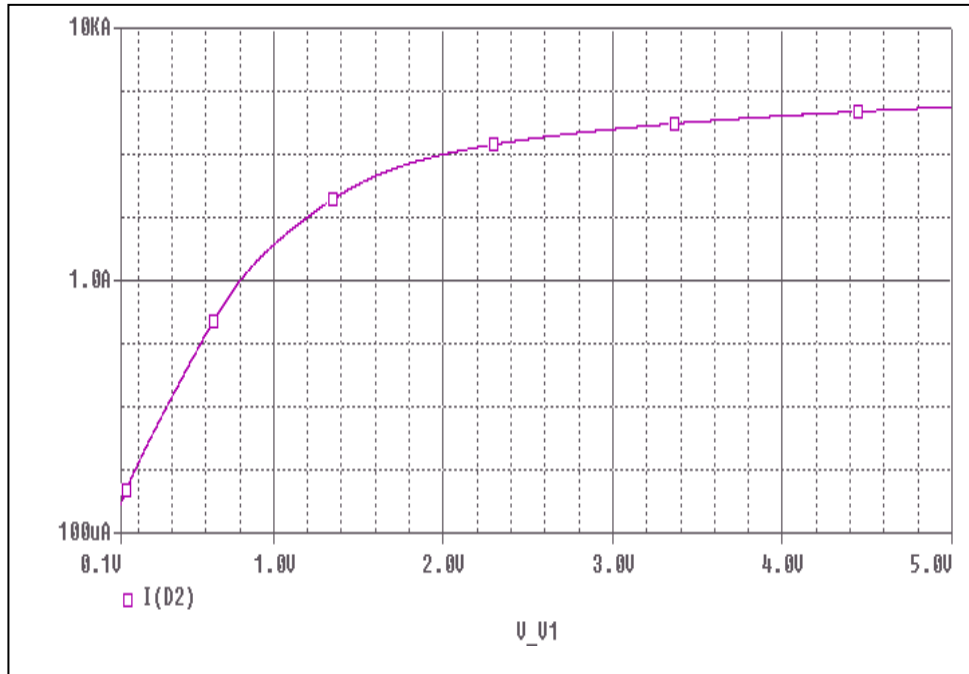


Bee Technologies Inc.

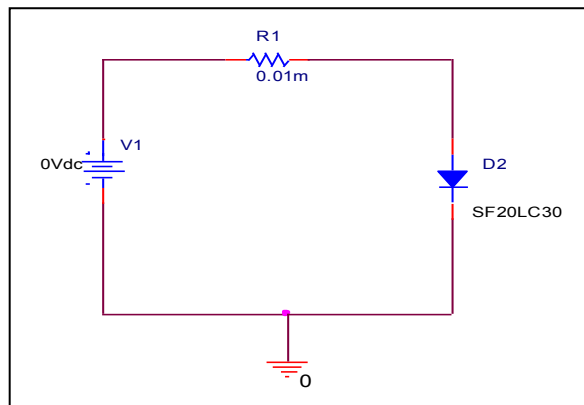
Pspice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time

Forward Current Characteristic

Circuit Simulation Result

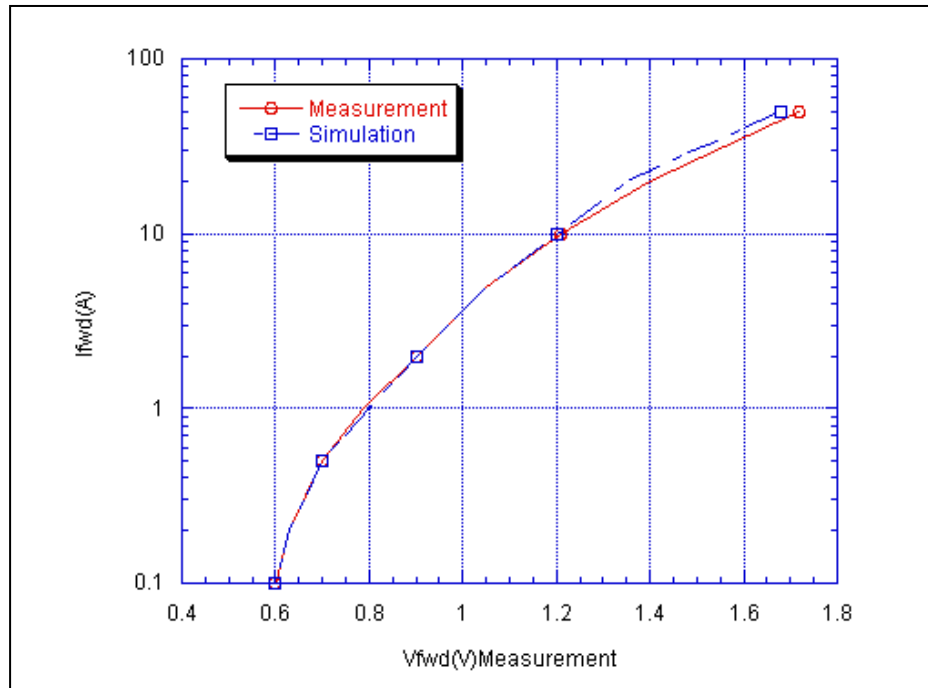


Evaluation circuit



Comparison graph

Circuit Simulation Result

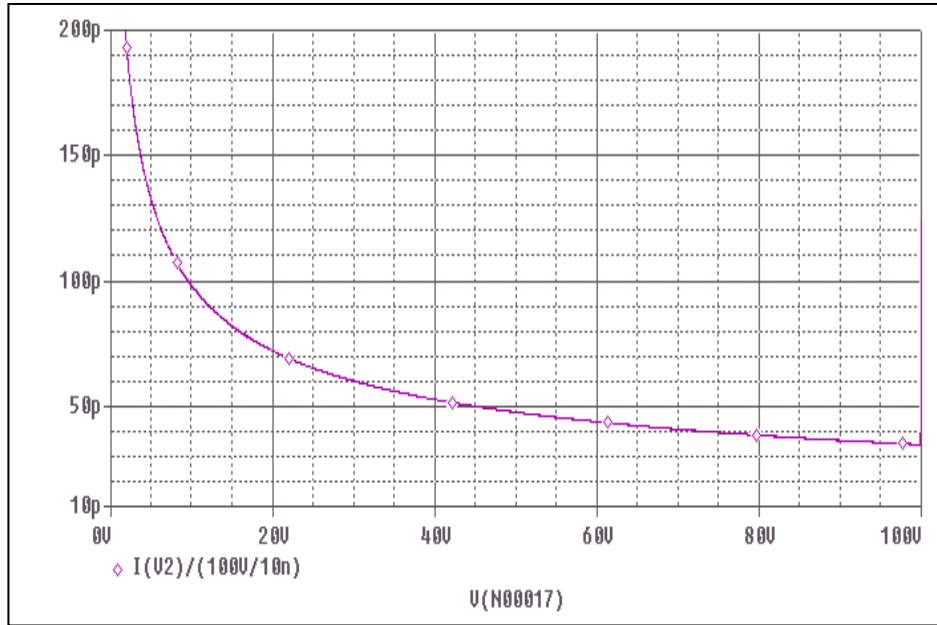


Simulation Result

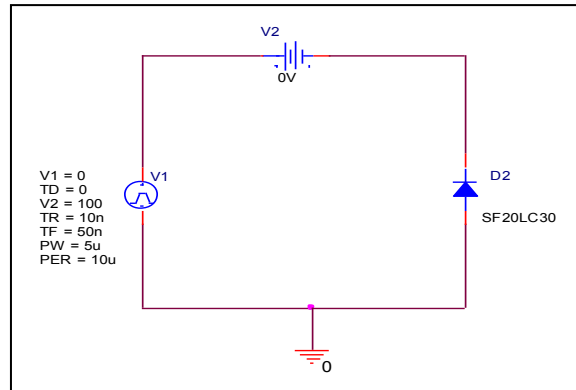
Ifwd (A)	Vfwd (V) Measurement	Vfwd (V) Simulation	%Error
0.1	0.600	0.600	0.00
0.2	0.630	0.630	0.00
0.5	0.700	0.700	0.00
1	0.790	0.800	-1.27
2	0.900	0.900	0.00
5	1.050	1.050	0.00
10	1.210	1.200	0.83
20	1.400	1.350	3.57
50	1.720	1.680	2.33

Junction Capacitance Characteristic

Circuit Simulation Result

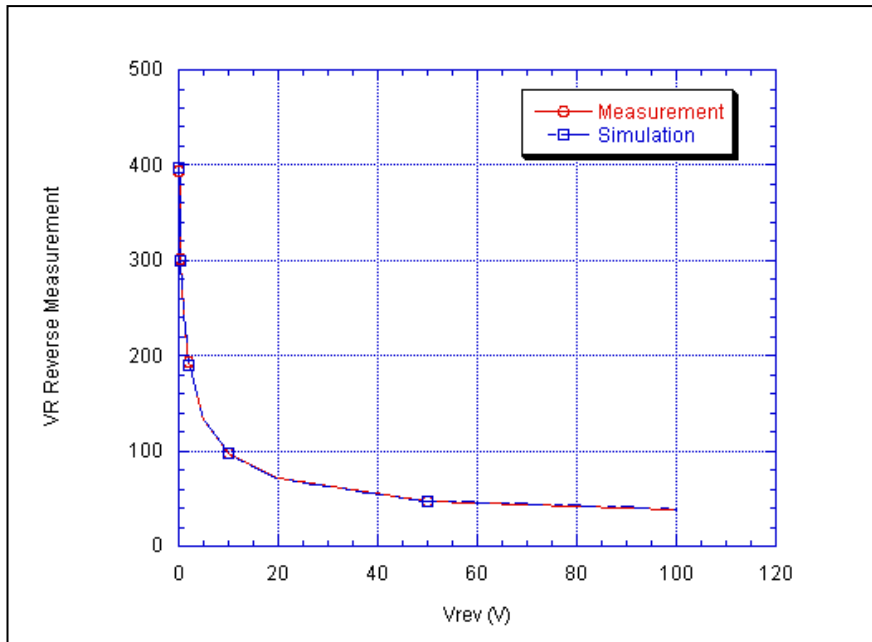


Evaluation circuit



Comparison graph

Circuit Simulation Result

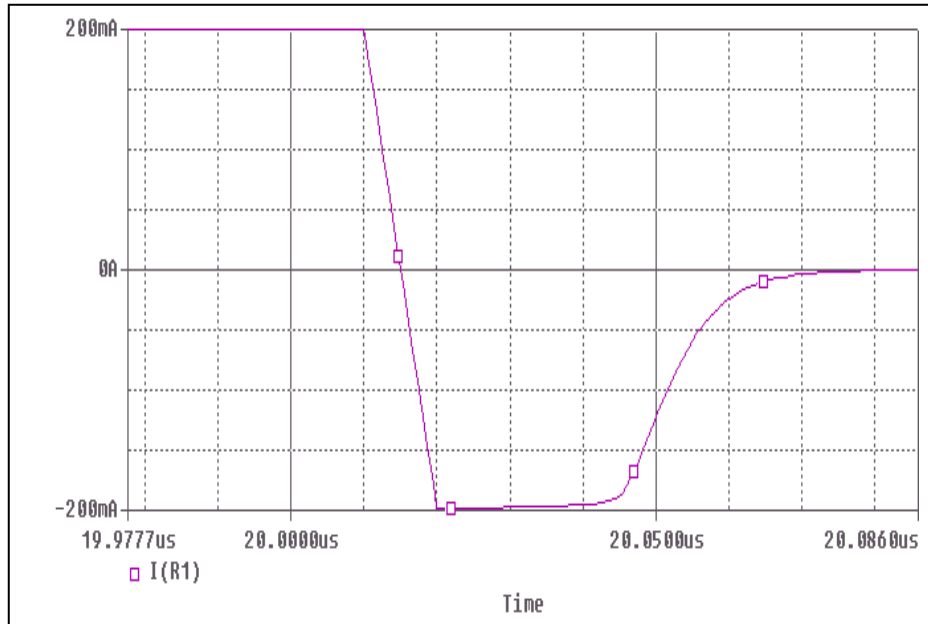


Simulation Result

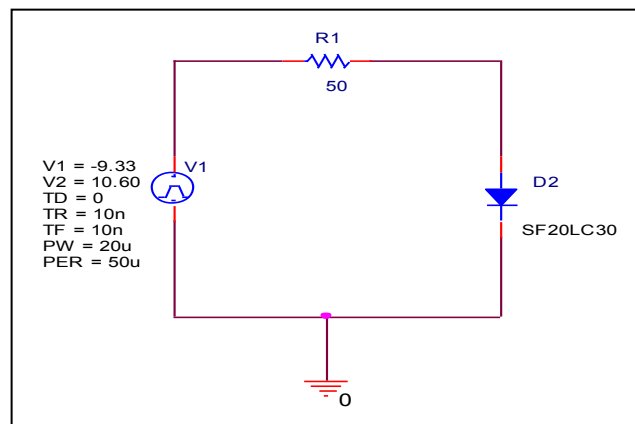
Vrev (V)	Cj(pF) Measurement	Cj(pF) Simulation	%Error
0	437.320	437.320	0.00
0.1	393.370	396.850	-0.88
0.2	369.930	365.148	1.29
0.5	301.080	299.224	0.62
1	244.790	247.844	-1.25
2	192.800	190.064	1.42
5	133.090	132.941	0.11
10	97.618	98.170	-0.57
20	71.454	71.454	0.00
50	46.989	47.535	-1.16
100	38.119	37.734	1.01

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation circuit

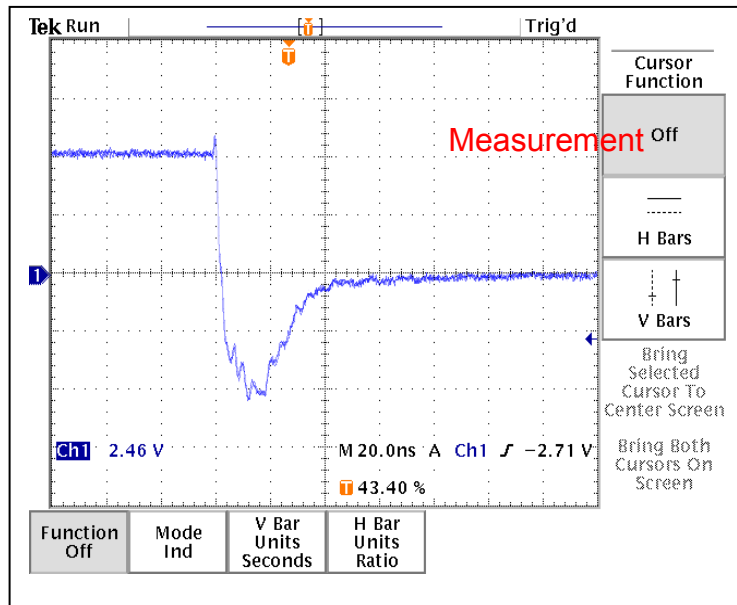


Compare Measurement vs. Simulation

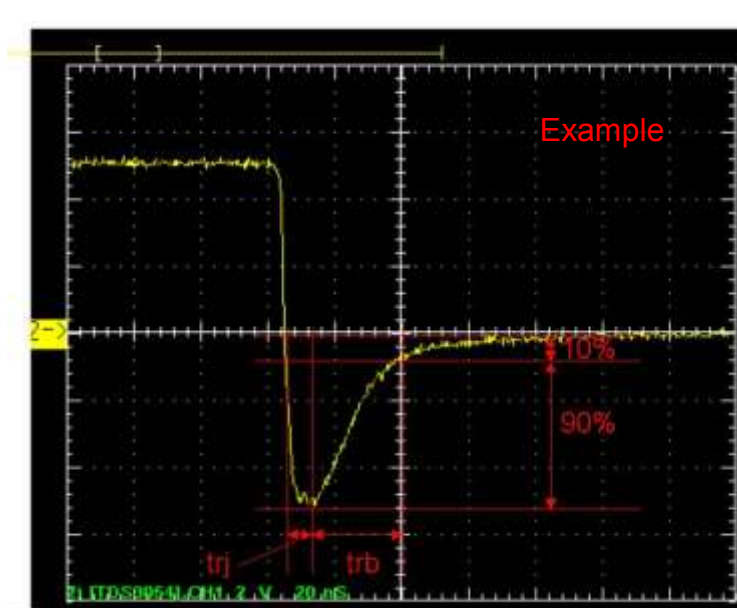
	Measurement		Simulation		%Error
trr	44.80	ns	45.00	ns	0.44

Reverse Recovery Characteristic

Reference



$tr_j=14.8(ns)$
 $tr_b=30.0(ns)$
Conditions: $I_{fwd}=I_{rev}=0.2(A)$, $R_I=50$



Relation between tr_j and tr_b